Yuanzhong Zhou

List of Publications by Year
in descending order

30	197	1307594 7	1125743 13
papers	citations	h-index	g-index

30	30	30	97
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	High-Robustness and Low-Capacitance Silicon-Controlled Rectifier for High-Speed I/O ESD Protection. IEEE Electron Device Letters, 2013, 34, 178-180.	3.9	40
2	Modeling and Simulation of Comprehensive Diode Behavior Under Electrostatic Discharge Stresses. IEEE Transactions on Device and Materials Reliability, 2019, 19, 90-96.	2.0	18
3	Compact Thermal Failure Model for Devices Subject to Electrostatic Discharge Stresses. IEEE Transactions on Electron Devices, 2015, 62, 4128-4134.	3.0	17
4	Prediction and Modeling of Thin Gate Oxide Breakdown Subject to Arbitrary Transient Stresses. IEEE Transactions on Electron Devices, 2010, 57, 2296-2305.	3.0	16
5	Gate oxide evaluation under very fast transmission line pulse (VFTLP) CDM-type stress. , 2008, , .		12
6	Optimizing high efficient plasma immersion ion implantation hydrogenation for poly-Si thin film transistors. Nuclear Instruments & Methods in Physics Research B, 1997, 124, 69-75.	1.4	10
7	ESD protection structure with reduced capacitance and overshoot voltage for high speed interface applications. Microelectronics Reliability, 2017, 79, 201-205.	1.7	10
8	Compact failure modeling for devices subject to electrostatic discharge stresses â€“ A review pertinent to CMOS reliability simulation. Microelectronics Reliability, 2015, 55, 15-23.	1.7	9
9	Fabrication of low dielectric constant materials for ULSI multilevel interconnection by plasma ion implantation. IEEE Electron Device Letters, 1998, 19, 420-422.	3.9	8
10	ESD Simulation using Compact Models: from I/O Cell to Full Chip. , 2007, , .		8
11	Compact Modeling of On-Chip ESD Protection Using Standard MOS and BJT Models. , 2006, , .		7
12	Plasma ion implantation hydrogenation of poly-Si CMOS thin-film transistors at low energy and high dose rate using an inductively-coupled plasma source. IEEE Transactions on Electron Devices, 1998, 45, 1324-1328.	3.0	6
13	Modeling of high voltage devices for ESD event simulation in SPICE. Microelectronics Journal, 2012, 43, 305-311.	2.0	6
14	Short-Time Hydrogen Passivation of Poly-Si CMOS Thin film Transistors by High Dose Rate Plasma Ion Implantation. Materials Research Society Symposia Proceedings, 1995, 396, 515.	0.1	4
15	N-Type Doping by Plasma Ion Implantation Using a PH₃ SDS System. Materials Research Society Symposia Proceedings, 1996, 438, 351.	0.1	4
16	Investigation on effectiveness of series gate resistor in CDM ESD protection designs. , 2013, , .		4
17	Characterization and Modeling of the Transient Safe Operating Area in LDMOS Transistors. , 2019, , .		4
18	Carbon Nitride (Cn_x) Films Formed by Ion Implantation into Thin Carbon Films. Materials Research Society Symposia Proceedings, 1995, 396, 255.	0.1	3

#	Article	IF	Citations
19	Plasma Immersion Ion Implantation Modification of Surface Properties of Polymer Material. Materials Research Society Symposia Proceedings, 1996, 438, 511.	0.1	3
20	vfTLP-VTH: A new method for quantifying the effectiveness of ESD protection for the CDM classification test. Microelectronics Reliability, 2013, 53, 196-204.	1.7	3
21	Plasma Ion Implantation for Flat Panel Displays. Materials Research Society Symposia Proceedings, 1996, 438, 321.	0.1	2
22	Investigations of Plasma Immersion Ion Implantation Hydrogenation for Poly-Si Tfts Using an Inductively Coupled Plasma Source. Materials Research Society Symposia Proceedings, 1996, 438, 357.	0.1	1
23	Plasma Chemistry Study of Plasma Ion Implantation Doping for Cmos Devices. Materials Research Society Symposia Proceedings, 1998, 510, 239.	0.1	1
24	Thermal failure and voltage overshoot models for diode behavior under electrostatic discharge stresses. , 2018, , .		1
25	Nitrogen Plasma Ion Implantation into Carbon Films Deposited by the Anodic Vacuum ARc. Materials Research Society Symposia Proceedings, 1995, 388, 281.	0.1	0
26	Anodic vacuum arc deposition of carbon and nitrogen containing carbon films. , 0, , .		0
27	Investigations of Plasma Immersion Ion Implantation Hydrogenation for Poly-Si Tfts Using an Inductively Coupled Plasma Source. Materials Research Society Symposia Proceedings, 1996, 439, 269.	0.1	0
28	Study of high efficient Plasma Immersion Ion Implantation hydrogenation for CMOS poly-Si TFTs using an ICP plasma source. , 0, , .		0
29	Hydrodynamic and analytical models for plasma immersion ion implantation with dielectric substrates. , 0, , .		0
30	Low-Dielectric Constant SiO(F,C) Films for ULSI Interconnections Prepared by CF4 Plasma Ion Implantation. Materials Research Society Symposia Proceedings, 1998, 511, 63.	0.1	0